

**Silicon PNP Power Transistor**

**2SA1169**

**DESCRIPTION**

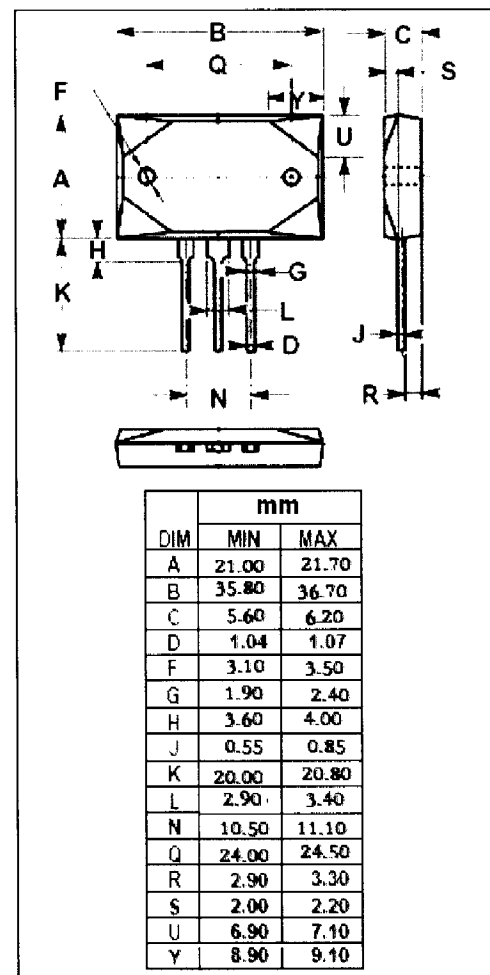
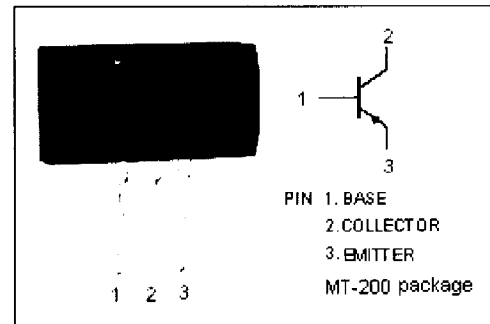
- Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -200V(\text{Min})$
- High Power Dissipation
- Complement to Type 2SC2773

**APPLICATIONS**

- Designed for power amplifier and general purpose applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-200	V
$V_{CEO}$	Collector-Emitter Voltage	-200	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-15	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	150	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1\text{mA}; I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -1\text{A}$			-2.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -200\text{V}; I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	30		200	
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f_{test} = 1.0\text{MHz}$		400		pF
$f_T$	Current-Gain—Bandwidth Product	$I_E = 1\text{A}; V_{CE} = -12\text{V}$		20		MHz